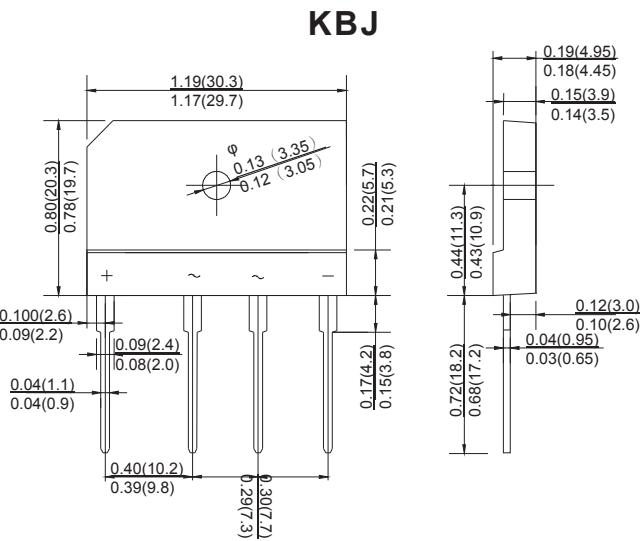


**SILICON BRIDGE RECTIFIER**
**VOLTAGE RANGE: 50 --- 1000 V**  
**CURRENT: 8.0 A**
**FEATURES**

- Rating to 1000V PRV
- Surge overload rating to 200 Amperes peak Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique results in inexpensive product
- Lead solderable per MIL-STD-202 method 208

**MECHANICAL DATA**

- Polarity:Sym bols molded on body
- Weight:0.23 ounces, 6.6 grams
- Mounting position: Any



Dimensions in inches and (millimeters)

**MAXIMUM RATINGS AND CHARACTERISTICS**

@ 25°C Ambient Temperature (unless otherwise noted)Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

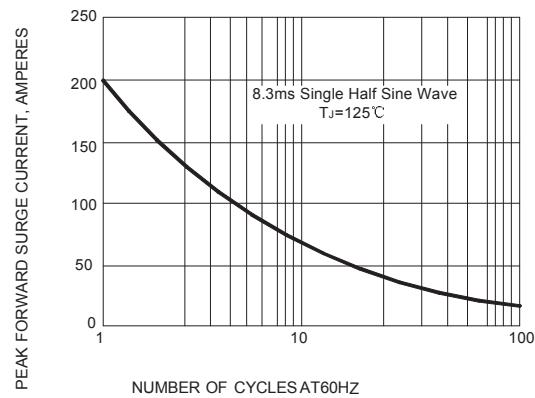
		KBJ 8A	KBJ 8B	KBJ 8D	KBJ 8G	KBJ 8J	KBJ 8K	KBJ 8M	UNITS
Maximum recurrent peak reverse voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS voltage	$V_{RMS}$	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	$V_{DC}$	50	100	200	400	600	800	1000	V
Maximum average forward Output current @ $T_A=110^\circ\text{C}$	$I_{F(AV)}$					8.0			A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load	$I_{FSM}$					200.0			A
Maximum instantaneous forward voltage at 4.0 A	$V_F$				1.0				V
Maximum reverse current @ $T_A=25^\circ\text{C}$ at rated DC blocking voltage @ $T_A=100^\circ\text{C}$	$I_R$				10.0				$\mu\text{A}$
Typical junction capacitance per element	$C_J$				1.0				mA
Typical thermal resistance	$R_{\theta JC}$				55				pF
Operating junction temperature range	$T_J$			- 55 ---- + 150					°C/W
Storage temperature range	$T_{STG}$			- 55 ---- + 150					°C

NOTES:1.Measured at 1.0MH<sub>z</sub> and applied reverse voltage of 4.0V DC

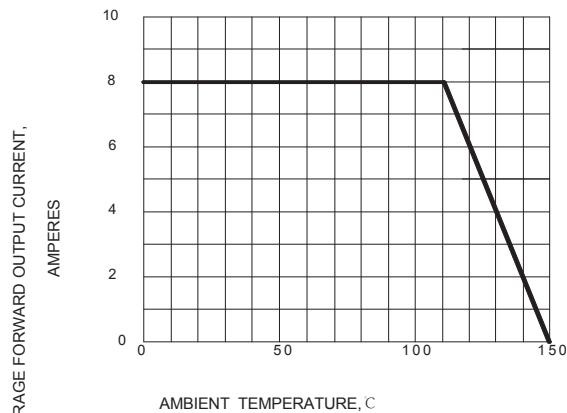
2.Device mounted on 300mm X 300mm X 1.6mm cu Plate heatsink.

## RATINGS AND CHARACTERISTIC CURVES

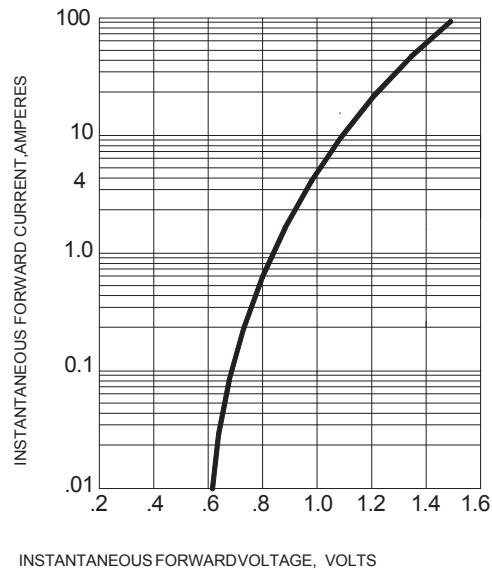
**FIG.1 – PEAK FORWARD SURGE CURRENT**



**FIG.2 – FORWARD DERATING CURVE**



**FIG.3 – TYPICAL FORWARD CHARACTERISTIC**



**FIG.4 – TYPICAL JUNCTION CAPACITANCE**

